

# Abstracts

## A New Approach to the RF Power Operation of MESFET's

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*G. Halkias, H. Gerard, Y. Crosnier and G. Salmer. "A New Approach to the RF Power Operation of MESFET's." 1989 Transactions on Microwave Theory and Techniques 37.5 (May 1989 [T-MTT]): 817-825.*

A new numerical large-signal model for a MESFET is described which allows investigations of the behavior of these devices at X-band frequencies under large-signal conditions. The results of the numerical simulations are compared with those of the measurements and provide an improved understanding of the behavior of GaAs MESFET's that operate at microwave frequencies and with high power requirements. Furthermore, our analysis yields some indications about the optimum design of these devices.

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